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| | | Application Number | W/804 514 |
| | | Filing Date | 03/19/2004 |
| | | First Named Inventor | Christine HOESS |
| | | Art Unit | 2823 |
| | | Examiner Name | T. PHAM |
| Sheet 1 of 2 | Attorney Docket Number | 5367-90 | |

| U.S. PATENT DOCUMENTS | | | | | |
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| Examiner Initials* | Cite No. ¹ | Document Number | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
| | | Number-Kind-Code ² (if known) | | | |
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| FOREIGN PATENT DOCUMENTS | | | | | | |
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| | | Country Code ² Number ³ Kind-Code ⁵ (if known) | | | | |
| WP | | JP 2001-015860 | 01/19/2001 | Fujitsu Ltd. | | ✓ |
| WP | | DE 101 47 791 A1 | 09/27/2001 | Osram Opto Semiconductors GmbH | | |
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| Examiner Signature | <i>Pham Thanh</i> | Date Considered | 09/14/2004 |
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| | | Filing Date | 03/19/2004 |
| | | First Named Inventor | Christine HOESS |
| | | Art Unit | 2823 |
| | | Examiner Name | T. PHAM |
| Sheet 2 of 2 | Attorney Docket Number | 5367-90 | |
| NON PATENT LITERATURE DOCUMENTS | | | |
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| TWP | | Tsuyoshi Tojyo, et al., "High-Power AlGaInN Laser Diodes with High Kink Level and Low Relative Intensity Noise", Jpn. J. Appl. Phys. Vol. 41, pp. 1829-1833, March 2002 | |
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| Examiner Signature | [Signature] | | Date Considered 03/19/2005 |

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